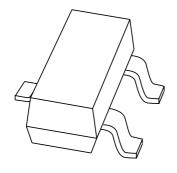
DISCRETE SEMICONDUCTORS

DATA SHEET



BC856; BC857; BC858 PNP general purpose transistors

Product specification Supersedes data of 2002 Feb 04 2003 Apr 09





PNP general purpose transistors

BC856; BC857; BC858

FEATURES

• Low current (max. 100 mA)

• Low voltage (max. 65 V).

APPLICATIONS

• General purpose switching and amplification.

DESCRIPTION

PNP transistor in a SOT23 plastic package. NPN complements: BC846, BC847 and BC848.

MARKING

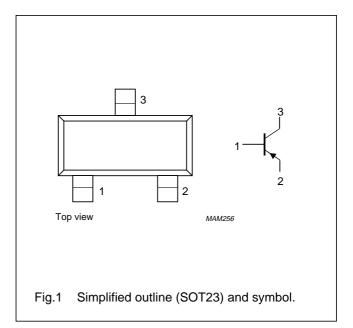
TYPE NUMBER	MARKING CODE(1)
BC856	3D*
BC856A	3A*
BC856B	3B*
BC857	3H*
BC857A	3E*
BC857B	3F*
BC857C	3G*
BC858B	3K*

Note

1. * = p: made in Hong Kong.

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



^{* =} t: made in Malaysia.

PNP general purpose transistors

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LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS		MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BC856		_	-80	V
	BC857		_	-50	V
	BC858		_	-30	V
V_{CEO}	collector-emitter voltage	open base			
	BC856		_	–65	V
	BC857		_	–45	V
	BC858		_	-30	V
V _{EBO}	emitter-base voltage	open collector	_	- 5	٧
I _C	collector current (DC)		_	-100	mA
I _{CM}	peak collector current		_	-200	mA
I _{BM}	peak base current		_	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	PARAMETER CONDITIONS		UNIT	
R _{th j-a}	thermal resistance from junction to ambient	in free air; note 1	500	K/W	

Note

1. Transistor mounted on an FR4 printed-circuit board, standard footprint.

^{1.} Transistor mounted on an FR4 printed-circuit board, standard footprint.

PNP general purpose transistors

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

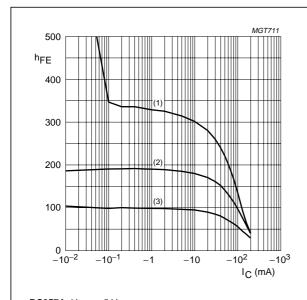
SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT	
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0$	_	-1	-15	nA
		$V_{CB} = -30 \text{ V}; I_E = 0;$ $T_j = 150 \text{ °C}$	_	_	-4	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$				
	BC856		125	_	475	
	BC857		125	_	800	
	BC856A; BC857A		125	_	250	
	BC856B; BC857B; BC858B		220	_	475	
	BC857C		420	_	800	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-75	-300	mV
		$I_C = -100 \text{ mA}; I_B = -5 \text{ mA};$ note 1	_	-250	-650	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	_	-700	_	mV
		$I_C = -100 \text{ mA}$; $I_B = -5 \text{ mA}$; note 1	_	-850	_	mV
V_{BE}	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	-650	-750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	_	_	-820	mV
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0;$ f = 1 MHz	_	4.5	_	pF
f _T	transition frequency	V _{CE} = -5 V; I _C = -10 mA; f = 100 MHz	100	-	-	MHz
F	noise figure	$I_{C} = -200 \mu A; V_{CE} = -5 V;$ $R_{S} = 2 k\Omega; f = 1 kHz;$ B = 200 Hz	_	2	10	dB

Note

1. Pulse test: $t_p \le 300~\mu s;~\delta \le 0.02.$

PNP general purpose transistors

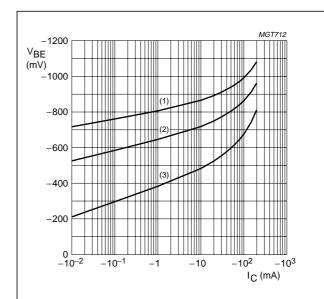
BC856; BC857; BC858



BC857A; $V_{CE} = -5 \text{ V}.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

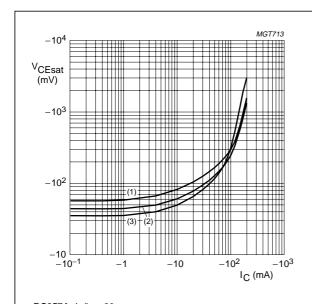
Fig.2 DC current gain as a function of collector current; typical values.



BC857A; $V_{CE} = -5 \text{ V}.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

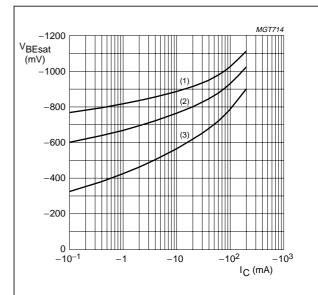
Fig.3 Base-emitter voltage as a function of collector current; typical values.



BC857A; $I_C/I_B = 20$.

- (1) T_{amb} = 150 °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



BC857A; $I_C/I_B = 20$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

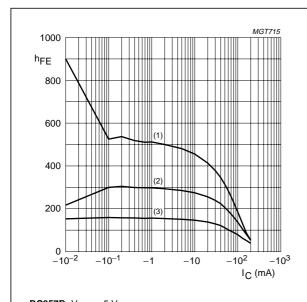
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Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.

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PNP general purpose transistors

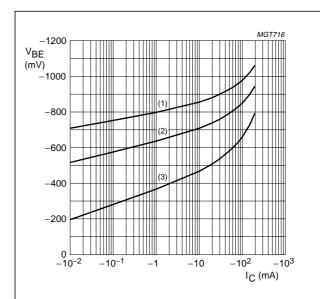
BC856; BC857; BC858



BC857B; $V_{CE} = -5 \text{ V}.$

- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

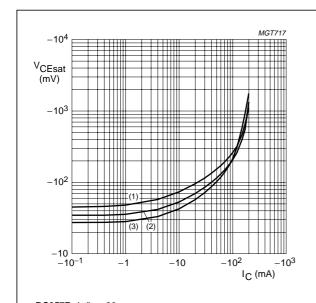
Fig.6 DC current gain as a function of collector current; typical values.



BC857B; $V_{CE} = -5 V$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

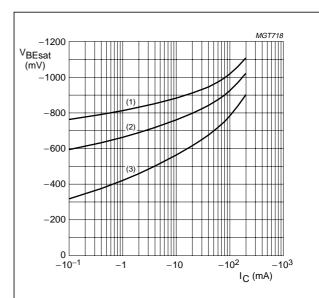
Fig.7 Base-emitter voltage as a function of collector current; typical values.



BC857B; $I_C/I_B = 20$.

- (1) T_{amb} = 150 °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.



BC857B; $I_C/I_B = 20$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

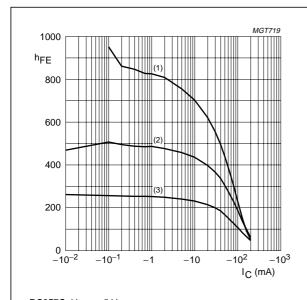
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Fig.9 Base-emitter saturation voltage as a function of collector current; typical values.

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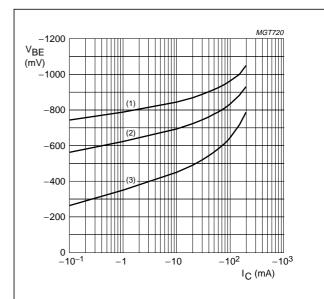
BC856; BC857; BC858



BC857C; $V_{CE} = -5 \text{ V}.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

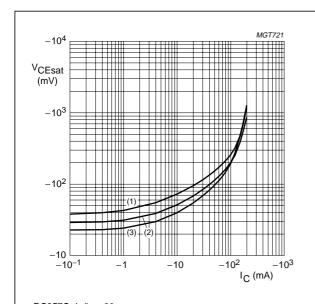
Fig.10 DC current gain as a function of collector current; typical values.



BC857C; $V_{CE} = -5 \text{ V}.$

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

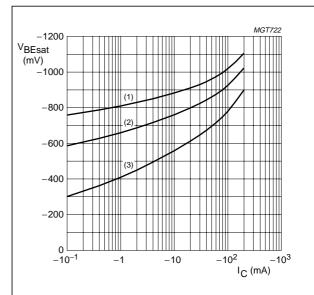
Fig.11 Base-emitter voltage as a function of collector current; typical values.



BC857C; $I_C/I_B = 20$.

- (1) T_{amb} = 150 °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.12 Collector-emitter saturation voltage as a function of collector current; typical values.



BC857C; $I_C/I_B = 20$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.13 Base-emitter saturation voltage as a function of collector current; typical values.

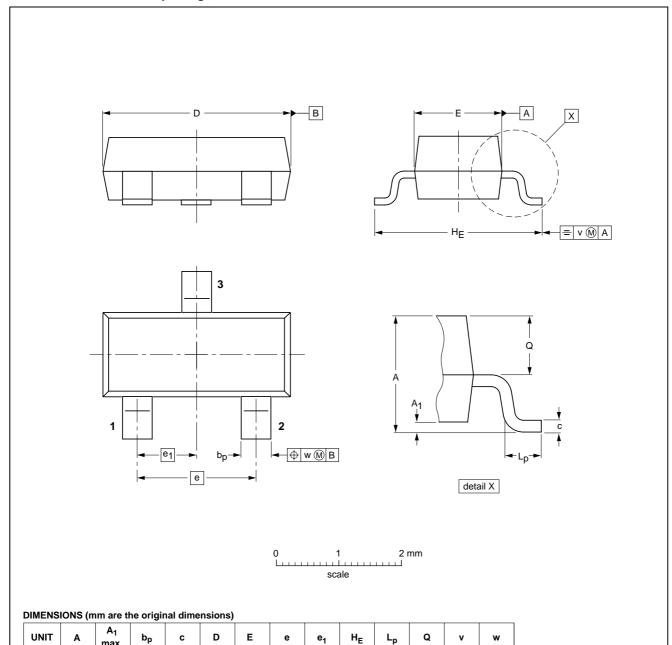
PNP general purpose transistors

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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT23		TO-236AB				97-02-28 99-09-13

0.95

0.45 0.15 0.55 0.45

0.1

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0.48

0.38

0.1

mm

0.15

0.09

3.0 2.8 1.4 1.2

1.9

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